# JIANGSU CHANGJING ELECTRONICS TECHNOLOGY CO., LTD JSCJ Plastic-Encapsulate Darlington Transistors

## ULN2003 DARLINGTON TRANSISTOR (NPN)

#### Description

ULN2003 is high voltage, high current darlington arrays each containing seven open collector darlington pairs with common emitters. Each channel rated at 500mA and can withstand peak currents of 600mA. Suppression diodes are included for inductive load driving and the inputs are pinned opposite the outputs to simplify board layout.

Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers. The ULN2003 device has a 2.7-k $\Omega$  series base resistor for each Darlington pair for operation directly with TTL or 5-V CMOS devices.

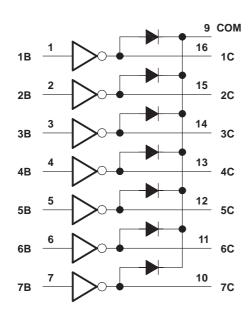
#### Features

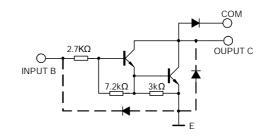
- 500-mA-Rated Collector Current (Single Output)
- High-Voltage Outputs: 40 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay-Driver Applications

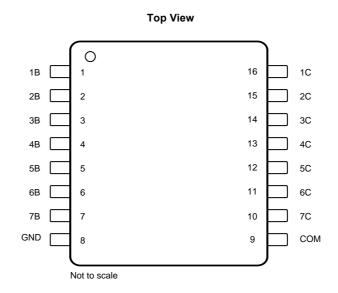
#### Applications

- Relay Drivers
- Hammer Drivers
- Lamp Drivers
- Line Drivers
- Logic Buffers
- Stepper Motors
- IP Camera
- HVAC Valve and LED Dot Matrix

## Logic Diagram







#### **Pin Functions**

PIN		TYPE	DESCRIPTION		
NAME	NO.	ITPE	DESCRIPTION		
1B	1				
2B	2				
3B	3				
4B	4	I	Channel 1 through 7 Darlington base input		
5B	5				
6B	6				
7B	7				
1C	16				
2C	15				
3C	14				
4C	13	0	Channel 1 through 7 Darlington collector output		
5C	12				
6C	11				
7C	10				
GND	8	_	Common emitter shared by all channels (typically tied to ground)		
COM	9	I/O	Common cathode node for flyback diodes (required for inductive loads)		

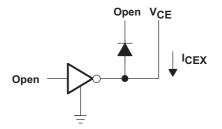
## **Typical Characteristics**

### **ABSOLUTE MAXIMUM RATING**

PARAMETER	SYMBOL		ULN2003			
PARAMETER	STMBOL	MIN	TYP	MAX	UNIT	
Output voltage	Vo			40	V	
Input voltage	VI			30	V	
Collector current(continuous current)	Ι <sub>C</sub>			500	mA	
Base current(continuous current)	Ι <sub>Β</sub>			25	mA	
Operating Ambient Temperature	T <sub>A</sub>	-20		85	°C	
Operating Junction Temperature	TJ			150	°C	
Storage Temperature	T <sub>stg</sub>	-55		150	°C	

## ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

PARAMETER		TEAT OF		ULN2003			
		TEST CONDITIONS		MIN	TYP	MAX	UNIT
1	Collector cutoff current	V <sub>CE</sub> = 40 V,	V <sub>CE</sub> = 40 V, Tamb=+85°C			100.0	μA
I <sub>CEX</sub>		V <sub>CE</sub> = 40 V, Tamb=+25°C				50.0	μA
		I <sub>C</sub> = 350 m	hA, Iв=500uA		1.1	1.6	
V <sub>CES</sub>	Collector-emitter saturation voltage	Ic = 200 mA, IB=350uA			0.95	1.3	V
		Ic = 100 mA, Iв=250uA			0.85	1.1	
II <sub>(ON)</sub>	Input current(ON)	V <sub>1</sub> = 3.85 V			0.93	1.35	mA
VI <sub>(ON)</sub>	Input voltage(ON)	V <sub>CE</sub> = 2.0 V, I <sub>C</sub> =200mA				2.4	v
		V <sub>CE</sub> = 2.0 V, I <sub>C</sub> =250mA				2.7	
		V <sub>CE</sub> = 2.0 V, I <sub>C</sub> =300mA				3.0	
II <sub>(OFF)</sub>	Input current(OFF)	V <sub>CE</sub> = 2.0	V, I <sub>C</sub> =350mA	50	100		μA
CI	Input capacitance				15	30	pF
t <sub>ON</sub>	On delay time	50%EI to 50% EO			0.25	1.0	μS
t <sub>OFF</sub>	Off delay time	50%EI to 50% EO			0.25	1.0	μS
I <sub>R</sub>		V <sub>R</sub> = 50 V	TA=+25°C			50.0	μA
	Clamp reverse current		TA=+85°C			100.0	
V <sub>F</sub>	Clamp forward voltage	IF=350mA			1.5	2.0	V





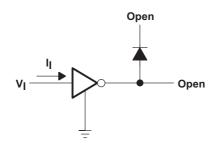
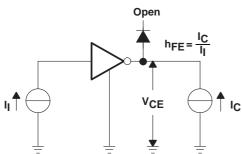


Figure 3. I<sub>I(on)</sub> Test Circuit



NOTE: I<sub>I</sub> is fixed for measuring V<sub>CE(sat)</sub>, variable for measuring hFE.



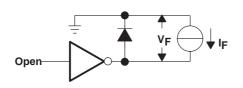


Figure 7. V<sub>F</sub> Test Circuit

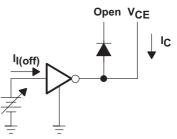


Figure 2. I<sub>I(off)</sub> Test Circuit

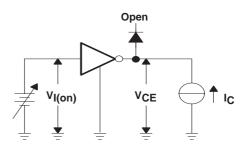


Figure 4. V<sub>I(on)</sub> Test Circuit

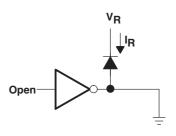
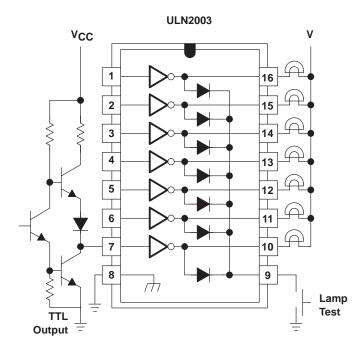


Figure 6. I<sub>R</sub> Test Circuit





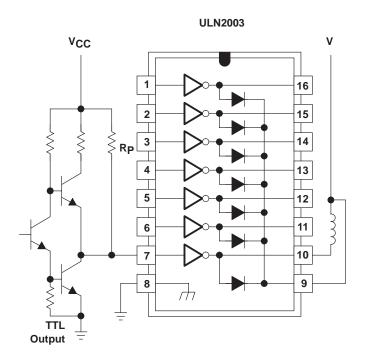
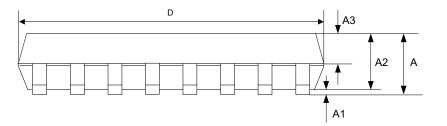
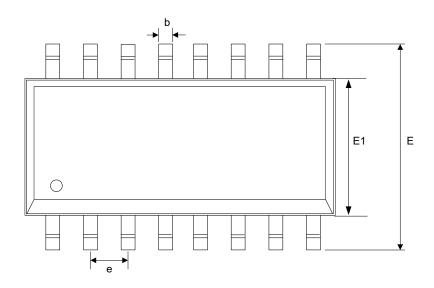
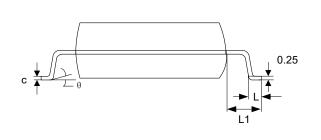


Figure 9. Use of Pullup Resistors to Increase Drive Current

# SOP-16 Package Outline Dimensions

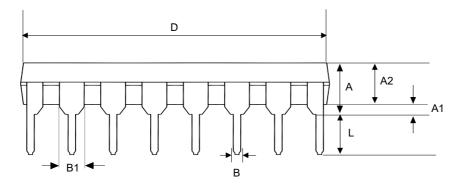


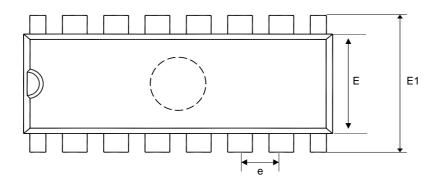


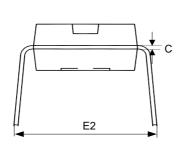


	MILLIMETER				
SYMBOL	MIN	NOM	MAX		
А	-	-	1.75		
A1	0.10	-	0.25		
A2			1.60		
A3	0.97	1.02	1.07		
b	0.35	-	0.46		
с	0.19	-	0.25		
D	9.80		10.0		
Е	5.80	6.00	6.20		
E1	3.80		4.00		
е	1.27BSC				
L	0.70	0.5	1.00		
L1	1.40BSC				
θ	0	-	8 °		

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GVMDOL	MILLIMETER			
SYMBOL	Min	Max		
А	3.710	4.310		
A1	0.510			
A2	3.200	3.600		
В	0.380	0.570		
B1	1.524(BSC)			
С	0.204	0.360		
D	18.800	19.200		
Е	6.200	6.600		
E1	7.320	7.920		
e	2.540(BSC)			
L	3.000	3.600		
E2	8.400	9.0070		

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